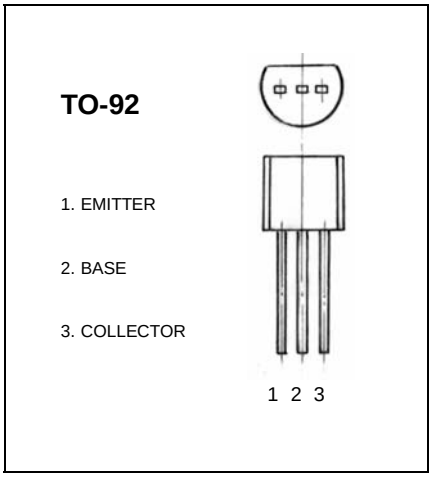
Transys Electronics LIMITED

TO-92 Plastic-Encapsulated Transistors

2N6727 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 1 W(Tamb=25℃)

Collector current

I_{CM} : -1.5 A

Collector-base voltage

$V_{(BR)CBO}$: -50 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= -1 mA, I_E=0	-50			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	I_C= -10 mA , I_B=0	-40			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= -1 mA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}= -50 V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}= -40 V, I_B=0			-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5 V, I_C=0			-0.1	μA
DC current gain	$H_{FE(1)}$	V_{CE}=-1 V, I_C= -1 A	50		250	
	$H_{FE(2)}$	V_{CE}=-1 V, I_C= -10 mA	55			
	$H_{FE(3)}$	V_{CE}=-1 V, I_C= -100 mA	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C= -1 A, I_B= -100 mA			-0.5	V
Base-emitter voltage	$V_{BE(on)}$	V_{CE}= -1 V, I_C= -1 A			-1.2	V
Transition frequency	f_T	V_{CE}=-10 V , I_C= -50 mA	50			MHz